

# Off-Line Current Mode PWM Control Circuit with Very Low Start Up Current

## Description

The CS384XB provides all the necessary features to implement off-line fixed frequency current-mode control with a minimum number of external components. The family has been optimized for very low start up current (300µA, typ).

The CS384XB family incorporates a precision temperature-controlled oscillator with an internally trimmed discharge current to minimize variations in frequency. A precision duty-cycle clamp eliminates the need for an external oscillator when a 50% duty-cycle is used. Duty-cycles of almost 100% are

possible. On board logic ensures that  $V_{REF}$  is stabilized before the output stage is enabled. Ion-implant resistors provide tighter control of undervoltage lockout.

Other features include pulse-by-pulse current limiting, and a high-current totem pole output for driving capacitive loads, such as the gate of a power MOSFET. The output is LOW in the off state, consistent with N-channel devices.

These ICs are available in 8 and 14 lead surface mount (SO) and 8 lead PDIP packages.

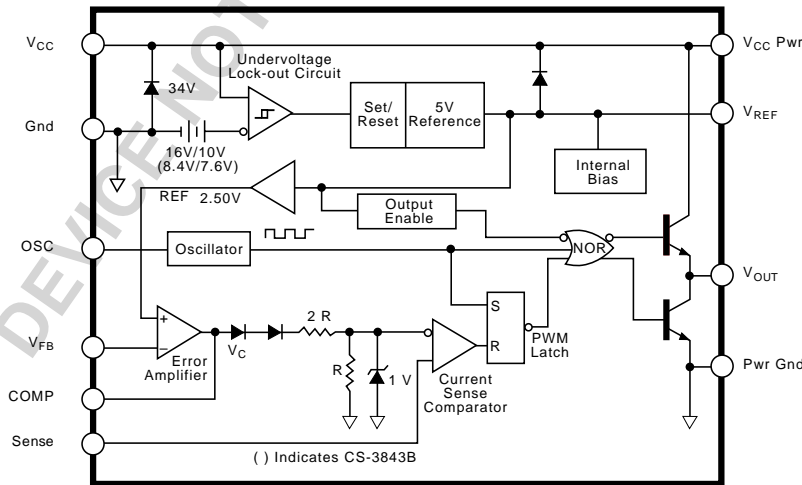
## Features

- Very low Start Up Current (300µA typ)
- Optimized Off-line Control
- Internally Trimmed, Temperature Compensated Oscillator
- Maximum Duty-cycle Clamp
- $V_{REF}$  stabilization before Output Enable
- Pulse-by-pulse Current Limiting
- Improved Undervoltage Lockout
- Double Pulse Suppression
- 1% Trimmed Bandgap Reference
- High Current Totem Pole Output

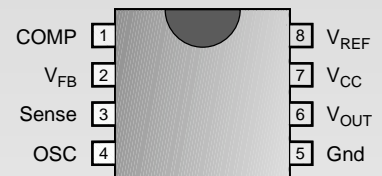
## Absolute Maximum Ratings

Supply Voltage ( $I_{CC} < 30mA$ )	.....	Self Limiting
Supply Voltage (Low Impedance Source)	.....	30V
Output Current	.....	±1A
Output Energy (Capacitive Load)	.....	5µJ
Analog Inputs ( $V_{FB}$ , Sense)	.....	-0.3V to 5.5V
Error Amp Output Sink Current	.....	10mA
Lead Temperature Soldering		
Wave Solder (through hole styles only)	.....	10 sec. max, 260°C peak
Reflow (SMD styles only)	.....	60 sec. max above 183°C, 230°C peak

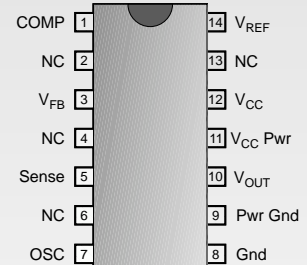
## Block Diagram



## 8 Lead PDIP & SO Narrow



## 14L SO Narrow



Electrical Characteristics:  $0 \leq T_A \leq 70^\circ\text{C}$ ,  $V_{CC}=15\text{V}$  (Note 1);  $R_T=680\Omega$ ,  $C_T=.022\mu\text{F}$  for triangular mode,  $R_T=10\text{k}\Omega$ ,  $C_T=3.3\text{nF}$  for sawtooth mode (see Fig. 3), unless otherwise stated

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>■ Reference Section</b>					
Output Voltage	$T_J=25^\circ\text{C}$ , $I_{OUT}=1\text{mA}$	4.90	5.00	5.10	V
Line Regulation	$12 \leq V_{IN} \leq 25\text{V}$		6	20	mV
Load Regulation	$1 \leq I_{OUT} \leq 20\text{mA}$		6	25	mV
Temperature Stability	(Note 2)		0.2	0.4	mV/ $^\circ\text{C}$
Total Output Variation	Line, Load, Temperature (Note 2)	4.82		5.18	V
Output Noise Voltage	$10\text{Hz} \leq f \leq 10\text{kHz}$ , $T_J=25^\circ\text{C}$ (Note 2)		50		$\mu\text{V}$
Long Term Stability	$T_A=125^\circ\text{C}$ , 1kHrs. (Note 2)		5	25	mV
Output Short Circuit	$T_A=25^\circ\text{C}$	-30	-100	-180	mA
<b>■ Oscillator Section</b>					
Initial Accuracy	Sawtooth Mode (see Fig. 3), $T_J=25^\circ\text{C}$	47	52	57	kHz
	Triangular Mode (see Fig. 3), $T_J=25^\circ\text{C}$	44	52	60	kHz
Voltage Stability	$12 \leq V_{CC} \leq 25\text{V}$		0.2	1.0	%
Temp. Stability	Sawtooth Mode $T_{MIN} \leq T_A \leq T_{MAX}$ (Note 2)		5		%
	Triangular Mode $T_{MIN} \leq T_A \leq T_{MAX}$ (Note 2)		8		%
Amplitude	Oscillator peak to peak		1.7		V
Discharge Current	$T_J=25^\circ\text{C}$	7.5	8.3	9.3	mA
	$T_{MIN} \leq T_A \leq T_{MAX}$	7.2		9.5	mA
<b>■ Error Amp Section</b>					
Input Voltage	$V_{COMP}=2.5\text{V}$	2.42	2.50	2.58	V
Input Bias Current			-0.3	-2.0	$\mu\text{A}$
$A_{VOL}$	$2 \leq V_{OUT} \leq 4\text{V}$	65	90		dB
Unity Gain Bandwidth	(Note 2)	0.7	1.0		MHz
PSRR	$12 \leq V_{CC} \leq 25\text{V}$	60	70		dB
Output Sink Current	$V_{FB}=2.7\text{V}$ , $V_{OSC}=1.1\text{V}$	2	6		mA
Output Source Current	$V_{FB}=2.3\text{V}$ , $V_{OSC}=5\text{V}$	-0.5	-0.8		mA
$V_{OUT}$ High	$V_{FB}=2.3\text{V}$ , $R_L=15\text{k}\Omega$ to ground	5	6		V
$V_{OUT}$ Low	$V_{FB}=2.7\text{V}$ , $R_L=15\text{k}\Omega$ to $V_{REF}$		0.7	1.1	V
<b>■ Current Sense Section</b>					
Gain	(Notes 3 & 4)	2.85	3.00	3.15	V/V
Maximum Input Signal	$V_{COMP}=5\text{V}$ (Note 3)	0.9	1.0	1.1	V
PSRR	$12 \leq V_{CC} \leq 25\text{V}$ (Note 3)		70		dB
Input Bias Current			-2	-10	$\mu\text{A}$
Delay to Output	$T_J=25^\circ\text{C}$ (Note 2)		150	300	ns
<b>■ Output Section</b>					
Output Low Level	$I_{SINK}=20\text{mA}$		0.1	0.4	V
	$I_{SINK}=200\text{mA}$		1.5	2.2	V
Output High Level	$I_{SOURCE}=20\text{mA}$	13.0	13.5		V
	$I_{SOURCE}=200\text{mA}$	12.0	13.5		V

## Electrical Characteristics: continued

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>■ Output Section: continued</b>					
Rise Time	$T_J=25^\circ\text{C}$ , $C_L=1\text{nF}$ (Note 2)		50	150	ns
Fall Time	$T_J=25^\circ\text{C}$ , $C_L=1\text{nF}$ (Note 2)		50	150	ns
Output Leakage	UVLO Active, $V_{OUT}=0$		-0.01	-10.00	$\mu\text{A}$

**■ Total Standby Current**

Start-Up Current			0.3	0.5	mA
Operating Supply Current	$V_{FB}=V_{Sense}=0\text{V}$ $R_T=10\text{k}\Omega$ , $C_T=3.3\text{nF}$		11	17	mA
$V_{CC}$ Zener Voltage	$I_{CC}=25\text{mA}$		34		V

PARAMETER	TEST CONDITIONS	CS-3842B			CS-3843B			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
<b>■ Under-Voltage Lockout Section</b>								
Start Threshold		14.5	16.0	17.5	7.8	8.4	9.0	V
Min. Operating Voltage	After Turn On	8.5	10.0	11.5	7.0	7.6	8.2	V

Notes: 1. Adjust  $V_{CC}$  above the start threshold before setting at 15V.  
 2. These parameters, although guaranteed, are not 100% tested in production.

3. Parameter measured at trip point of latch with  $V_{FB}=0$ .  
 4. Gain defined as:

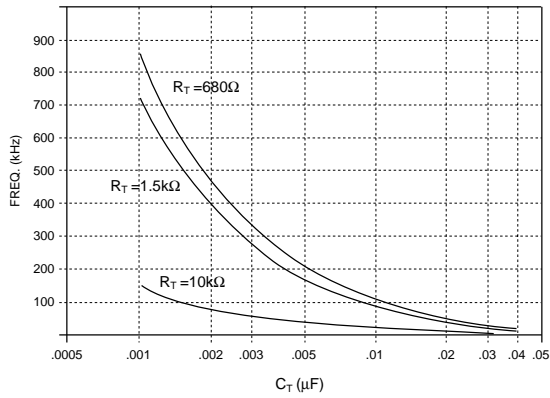
$$A = \frac{\Delta V_{COMP}}{\Delta V_{Sense}}; 0 \leq V_{Sense} \leq 0.8\text{V}.$$

## Package Pin Description

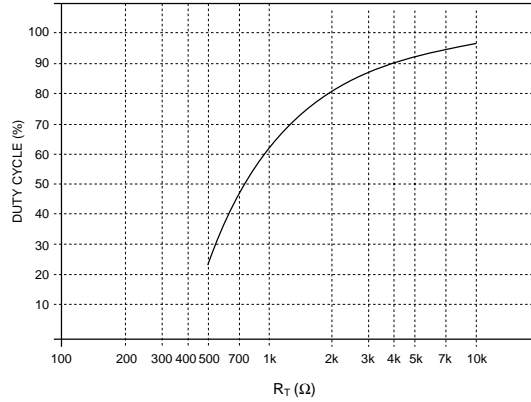
PACKAGE PIN #		PIN SYMBOL	FUNCTION
8L PDIP/SO	14L SO Narrow		
1	1	COMP	Error amp output, used to compensate error amplifier
2	3	$V_{FB}$	Error amp inverting input
3	5	Sense	Noninverting input to Current Sense Comparator
4	7	OSC	Oscillator Timing Network with Capacitor to Ground, resistor to $V_{REF}$
5	8	Gnd	Ground
	9	Pwr Gnd	Output driver Ground
6	10	$V_{OUT}$	Output drive pin
	11	$V_{CCPwr}$	Output driver positive supply
7	12	$V_{CC}$	Positive power supply
8	14	$V_{REF}$	Output of 5V internal reference
	2,4,6,13	NC	No Connection

Typical Performance Characteristics:

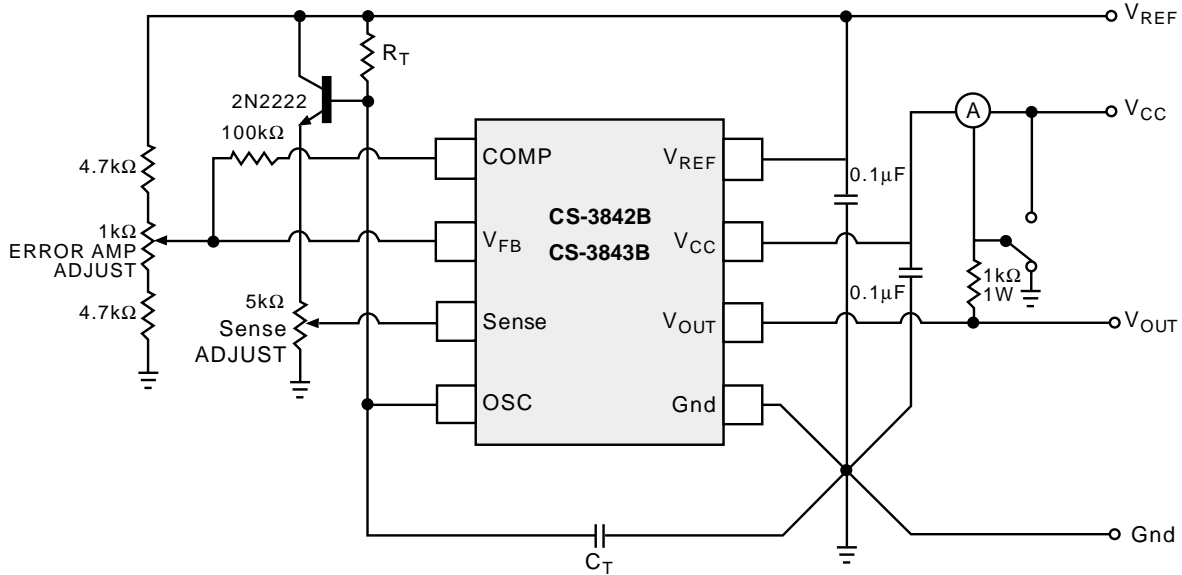
Oscillator Frequency vs  $C_T$



Oscillator Duty Cycle vs  $R_T$



Test Circuit



Circuit Description

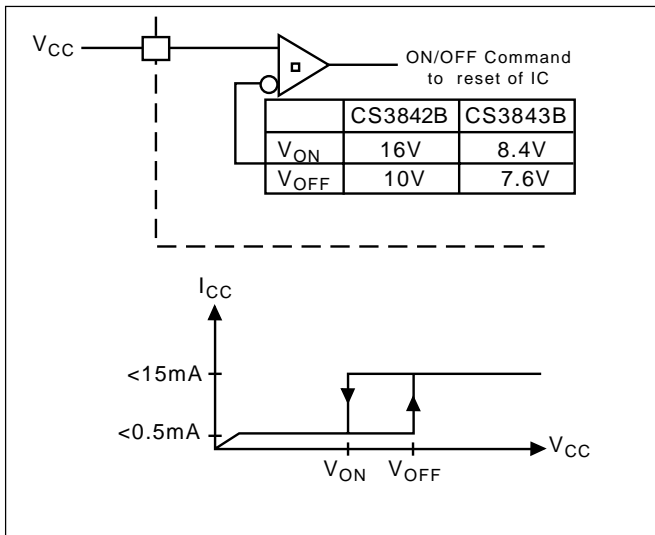


Figure 1: Typical Undervoltage Characteristics

Undervoltage Lockout

During Undervoltage Lockout (Figure 1), the output driver is biased to a high impedance state.  $V_{OUT}$  should be shunted to ground with a resistor to prevent output leakage current from activating the power switch.

PWM Waveform

To generate the PWM waveform, the control voltage from the error amplifier is compared to a current sense signal which represents the peak output inductor current (Figure 2). An increase in  $V_{CC}$  causes the inductor current slope to increase, thus reducing the duty cycle. This is an inherent feed-forward characteristic of current mode control, since the control voltage does not have to change during changes of input supply voltage.

When the power supply sees a sudden large output current increase, the control voltage will increase allowing the duty cycle to momentarily increase. Since the duty

Figure 3: Oscillator

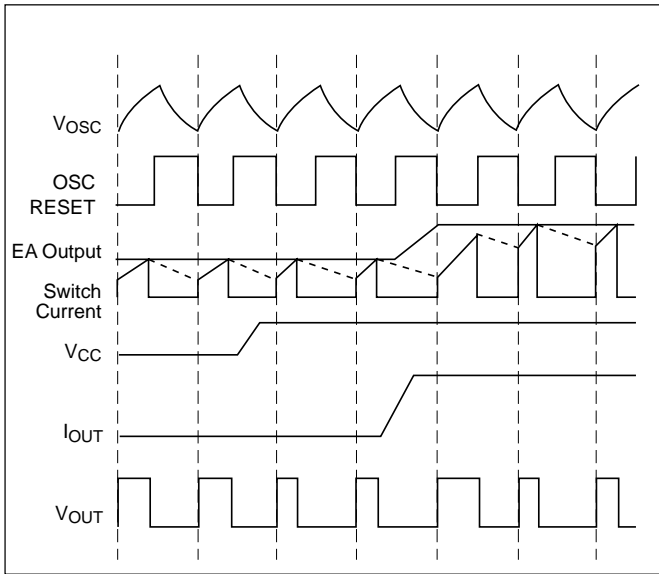


Figure 2: Timing Diagram for key CS-384XB parameters

cycle tends to exceed the maximum allowed, to prevent transformer saturation in some power supplies, the internal oscillator waveform provides the maximum duty cycle clamp as programmed by the selection of oscillator timing components.

### Setting the Oscillator

The oscillator timing capacitor,  $C_T$ , is charged by  $V_{REF}$  through  $R_T$  and discharged by an internal current source (Figure 3). During the discharge time, the internal clock signal blanks out the output to the Low state, thus providing a user selected maximum duty cycle clamp.

Charge and discharge times are determined by the general formulas:

$$t_c = R_T C_T \ln \left( \frac{V_{REF} - V_{lower}}{V_{REF} - V_{upper}} \right)$$

$$t_d = R_T C_T \ln \left( \frac{V_{REF} - I_d R_T - V_{lower}}{V_{REF} - I_d R_T - V_{upper}} \right)$$

Substituting in typical values for the parameters in the above formulas:

$V_{REF} = 5.0V, V_{upper} = 2.7V, V_{lower} = 1.0V, I_d = 8.3mA,$   
then

$$t_c \approx 0.5534 R_T C_T$$

$$t_d = R_T C_T \ln \left( \frac{2.3 - 0.0083 R_T}{4.0 - 0.0083 R_T} \right)$$

The frequency and maximum duty cycle can be determined from the Typical Performance Characteristics graphs.

### Grounding

High peak currents associated with capacitive loads necessitate careful grounding techniques. Timing and bypass capacitors should be connected close to ground in a single point ground.

The transistor and  $5k\Omega$  potentiometer are used to sample the oscillator waveform and apply an adjustable ramp to Sense.

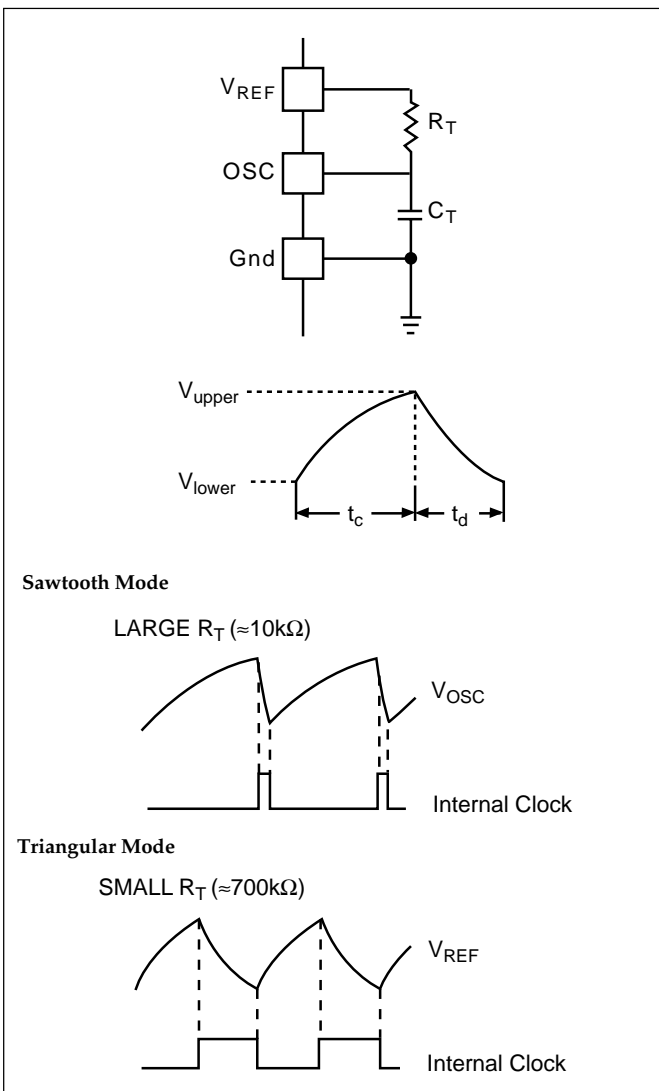


Figure 3: Oscillator Timing Network and parameters

## Package Specification

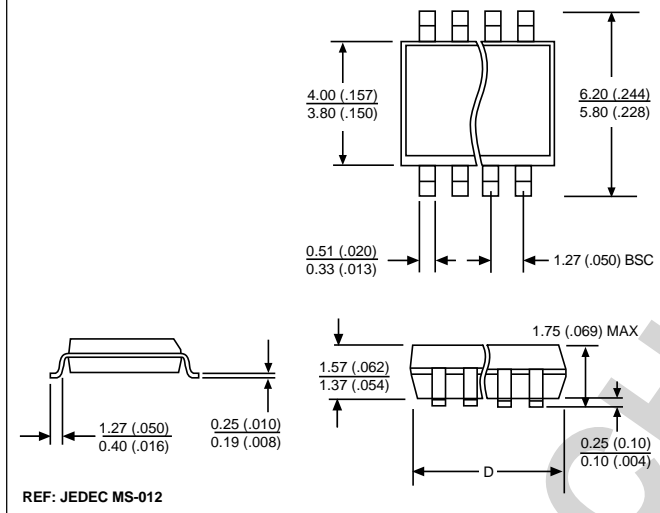
## PACKAGE DIMENSIONS IN mm (INCHES)

Lead Count	D			
	Metric		English	
	Max	Min	Max	Min
8 L PDIP	10.16	9.02	.400	.355
8 L SOIC Narrow	5.00	4.80	.197	.189
14L SOIC Narrow	8.75	8.55	.344	.337

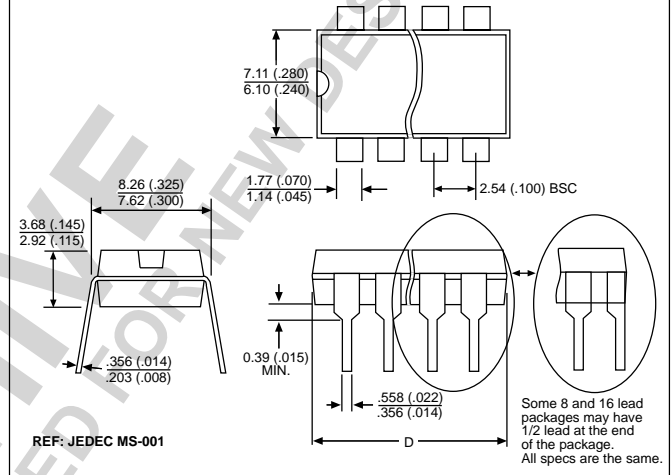
## PACKAGE THERMAL DATA

Thermal Data		8 L	8L	14 L	
		PDIP	SO Narrow	SO Narrow	
R $\theta_{JC}$	typ	52	45	30	°C/W
R $\theta_{JA}$	typ	100	165	125	°C/W

## Surface Mount Narrow Body (D); 150 mil wide



## Plastic DIP (N); 300 mil wide



## Ordering Information

Part Number	Description
CS3842BGN8	8L PDIP
CS3842BGD8	8L SO Narrow
CS3842BGDR8	8L SO Narrow (tape & reel)
CS3842BGD14	14L SO Narrow
CS3842BGDR14	14L SO Narrow (tape & reel)
CS3843BGN8	8L PDIP
CS3843BGD8	8L SO Narrow
CS3843BGDR8	8L SO Narrow (tape & reel)
CS3843BGD14	14L SO Narrow
CS3843BGDR14	14L SO Narrow (tape & reel)

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